

WHAT IS CLAIMED IS:

1. A semiconductor device comprising:
a metal plate for mounting a semiconductor chip;
a plurality of leads connected electrically to said semiconductor chip; and
a molding body for molding said semiconductor chip and a part of each of said plurality of leads,
wherein a slit, extending lengthwise in a direction in which said lead is extracted, is formed in each of said leads located outside said molding body.
2. A semiconductor device according to claim 1, wherein each of said leads is comprised of an inner lead and an outer lead, and said slit is formed only in said outer lead.
3. A semiconductor device according to claim 1, wherein each of said leads is comprised of an inner lead and an outer lead, and the outer lead of said lead is formed with a bent portion.
4. A semiconductor device according to claim 3, wherein said slit is formed in said bent portion.
5. A semiconductor device according to claim 1, wherein said metal plate is a heat sink.
6. A semiconductor device according to claim 1, wherein said molding body is formed of a resin for molding.
7. A semiconductor device according to claim 1, wherein each of said leads is comprised of an inner lead and an outer

lead, and those of a plurality of outer-lead split portions separated by said slits which are adjacent to each other are connected at respective tip portions thereof.

8. A semiconductor device according to claim 1, wherein an electrode of said semiconductor chip and each of said leads are electrically connected to each other by a metal wire.

9. A semiconductor device according to claim 1, wherein said metal plate and each of said leads have an overlapping portion therebetween.

10. A semiconductor device according to claim 1, wherein an output of said semiconductor chip is 30 watt or more.

11. A semiconductor device according to claim 1, wherein said semiconductor chip includes a MISFET and one of those two of said leads disposed in opposing relation is a gate electrode of said MISFET, while the other of those two of said leads is a drain electrode of said MISFET.

12. A semiconductor device comprising:

a metal plate for mounting a semiconductor chip;

a plurality of leads each having an inner lead connected electrically to said semiconductor chip and an outer lead connecting to the inner lead and formed with a bent portion; and

a molding body for molding said semiconductor chip and a part of each of said plurality of leads, said molding body being formed of a resin for molding,

wherein a slit, extending lengthwise in a direction in

which said lead is extracted, is formed in each of said leads located outside said molding body, and

wherein said slit is formed in said bent portion, and those of a plurality of outer-lead split portions separated by said slits which are adjacent to each other are connected at respective tip portions thereof.

13. A semiconductor device comprising:

a metal plate for mounting a semiconductor chip, said metal plate having an edge portion formed with a depressed portion;

a plurality of leads connected electrically to said semiconductor chip; and

a molding body for molding said semiconductor chip and a part of each of said plurality of leads,

wherein each of said plurality of leads has one end disposed above said depressed portion of said metal plate.

14. A semiconductor device according to claim 13, wherein an insulator is disposed between each of said plurality of leads and said metal plate.

15. A semiconductor device according to claim 14, wherein said insulator is said molding body.

16. A semiconductor device according to claim 13, wherein said plurality of leads have respective inner leads disposed to be flush with a metal plate suspending portion for supporting said metal plate.

17. A method for manufacturing a semiconductor device comprising: a metal plate for mounting a semiconductor chip; a plurality of leads connected electrically to said semiconductor chip; and a molding body for molding said semiconductor chip and a part of each of said plurality of leads, in which a slit, extending lengthwise in a direction in which said lead is extracted, is formed in each of said leads located outside said molding body,

the method comprising the step of:

performing a screening test on said semiconductor device, wherein said slit is formed prior to said screening test.

18. A method for manufacturing a semiconductor device comprising: a metal plate for mounting a semiconductor chip; a plurality of leads connected electrically to said semiconductor chip; and a molding body for molding said semiconductor chip and a part of each of said plurality of leads, in which a slit, extending lengthwise in a direction in which said lead is extracted, is formed in each of said leads located outside said molding body,

the method comprising the step of:

forming a bent portion to an outer lead of said lead, wherein said slit is formed before the formation of said bent portion.

19. A method according to claim 18,

wherein each of said leads is comprised of an inner lead

and an outer lead, and

wherein said slit is formed only in the outer lead portion.